RESONANT RAMAN SCATTERING
IN
III-V ALLOY SEMICONDUCTORS

by

RAVI KANT SONI
Laser Technology Research Programme
Physics Department

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CERTIFICATE

This is to certify that the thesis entitled "Resonant Raman Scattering in III-V alloy semiconductors" which is being submitted by Mr. Ravi Kant Soni to the Indian Institute of Technology, New Delhi is a record of bonafide research work carried out by him under our guidance and supervision.

In our opinion this thesis has reached the standard fulfilling the requirements of all regulations relating to the degree. The results contained in it have not been submitted in part or in full to any other university or Institute for the award of any degree or diploma.

KPJain
3/10/82

(Dr. S.C. Abbi)
Assistant Professor
Deptt. of Physics
Indian Institute of
Technology New Delhi-16

(Prof. K.P. Jain)
Professor of Physics
&
Coordinator, Laser Technology Res. Programme
Indian Institute of Technology, Delhi-16.

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